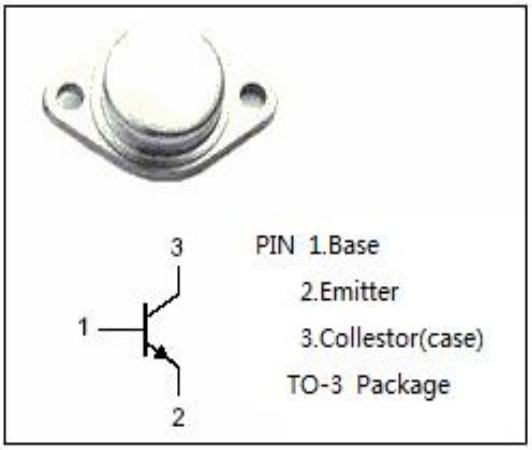
isc Silicon PNP Power Transistor NTE388

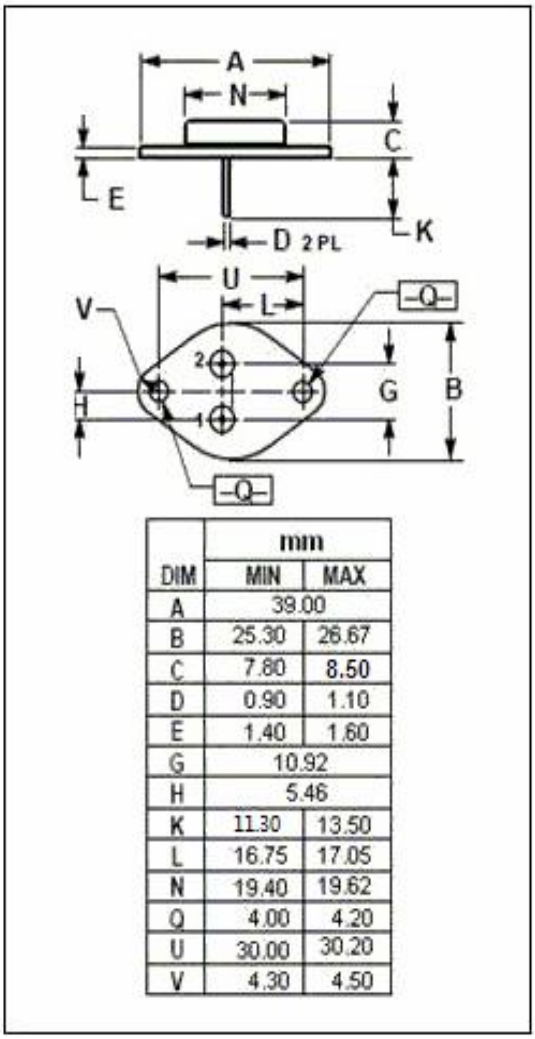
DESCRIPTION

- With TO-3 packaging
- Large collector current
- Low collector saturation voltage
- High power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for use in DC-DC converter
- Driver of solenoid or motor



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	16	A
I_{CP}	Collector Current-Pulse	30	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ T_C=25℃	33	W
	Collector Power Dissipation @ T_a=25℃	0.26	
T_J	Junction Temperature	-65~200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 800mA			1.4	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 16A; I_B= 3.2A			4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 8A; V_{CE}=4V			2.2	V
V_{CBO}	Collector-Base Breakdown Voltage	I_C= 1mA; I_B= 0	400			
V_{CEO}	Collector-Emitter Breakdown Voltage	I_C=100mA;I_E=0	250			
V_{EBO}	Emitter-Base Breakdown Voltage	I_E=1mA;I_B= 0	5			
I_{CEO}	Collector Cutoff Current	V_{CE}= 200V; I_E= 0			500	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}=5V; I_C= 0			500	μA
h_{FE-1}	DC Current Gain	I_C=8A; V_{CE}=4V	15		60	
h_{FE-2}	DC Current Gain	I_C=16A; V_{CE}=4V	5			